

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring enhanced immunity to noise and direct interfacing to logic level ICs and low power gate drivers.

2. Features and benefits

- Direct interfacing to logic level ICs
- · Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate in four quadrants
- Surface-mountable package
- Triggering in all four quadrants

3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- · Low power AC Fan controllers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage			-	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 105 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>		-	-	1	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>		-	-	12.5	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms		-	-	13.8	A
Tj	junction temperature			-	-	125	°C
Static chara	cteristics		-			-	
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>		0.4	-	10	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	0.4	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 9</u>	0.4	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 9</u>	0.4	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
Dynamic ch	aracteristics	·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 110 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit; Fig. 14	120	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T _j = 110 °C; dI _{com} / dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

5. Pinning information

Table 2.	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2-71
2	T2	main terminal 2		G sym051
3	G	gate		Symoor
4	T2	main terminal 2	☐1 ☐2 ☐ 3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
Z0109NN0	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223				

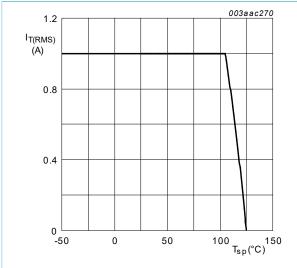


7. Limiting values

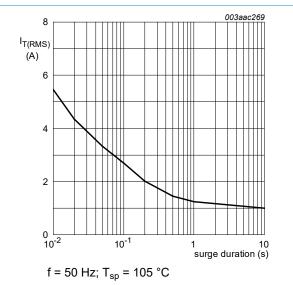
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 105 °C; <u>Fig. 1; Fig. 2;</u> <u>Fig. 3</u>	-	1	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	12.5	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	13.8	А
l ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.78	A²s
dl _T /dt	rate of rise of on-state	I _G = 20 mA; T2+ G+	-	50	A/µs
	current	I _G = 20 mA; T2+ G-	-	50	A/µs
		I _G = 20 mA; T2- G-	-	50	A/µs
		I _G = 20 mA; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	А
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

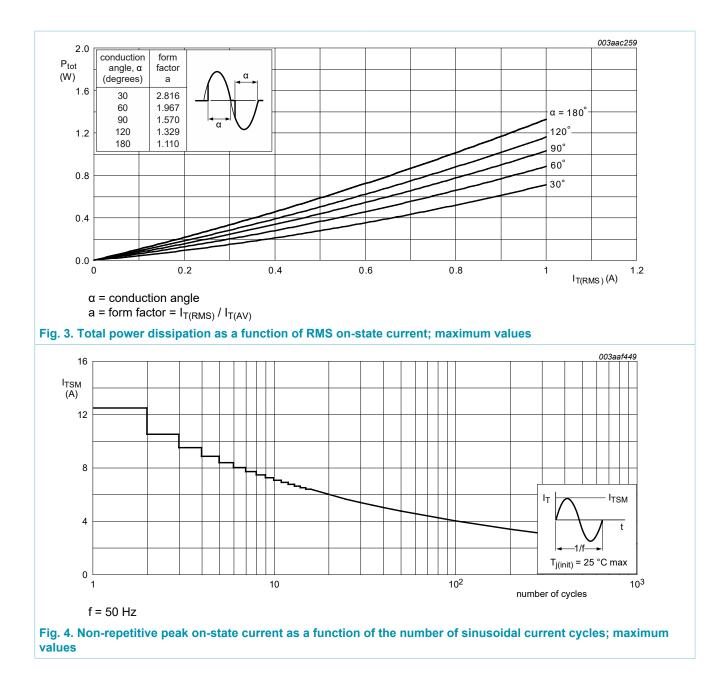






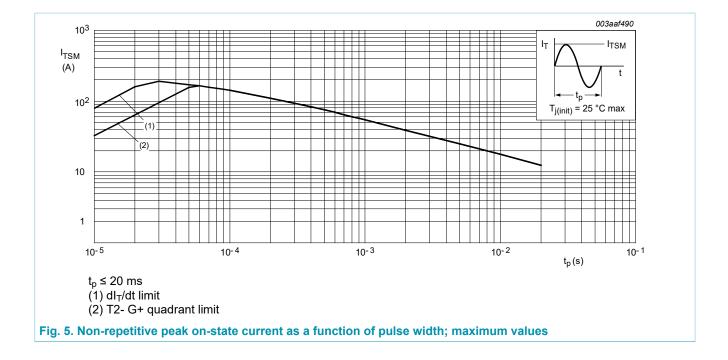


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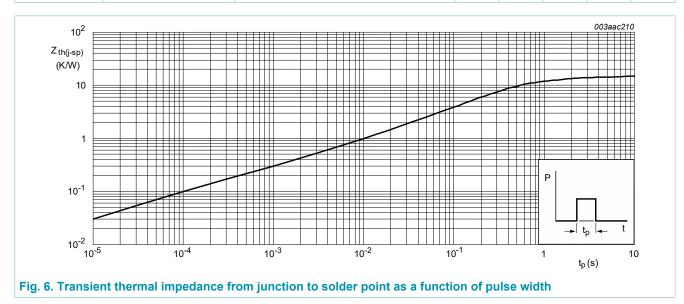
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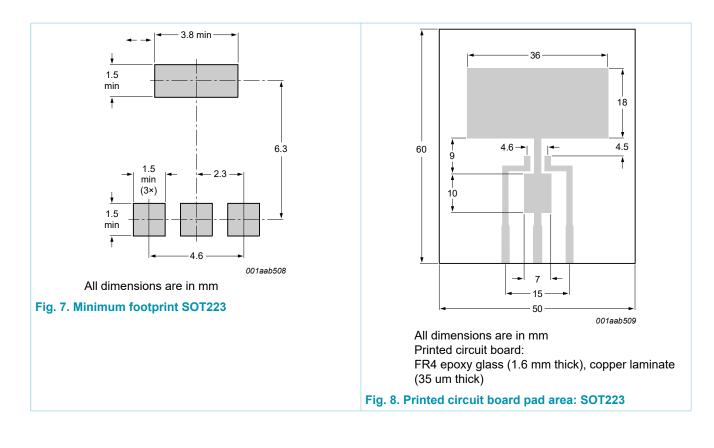
8. Thermal characteristics

Table 5. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; <u>Fig. 6</u>	-	-	15	K/W
fr	thermal resistance from junction to ambient free air	in free air; printed-circuit board mounted: minimum footprint; full cycle; Fig. 7	-	156	-	K/W
		in free air; printed-circuit board mounted: pad area; full cycle; Fig. 8	-	70	-	K/W



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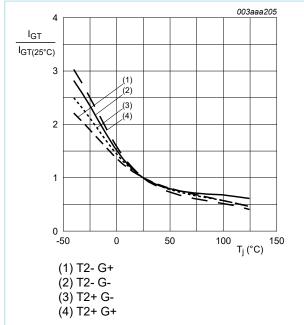


9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		· · · · ·			,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G+};$ T _j = 25 °C; Fig. 9	0.4	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; Fig. 9	0.4	-	10	mA
		$V_D = 12 V; I_T = 0.1 A; T2- G-;$ $T_j = 25 °C; Fig. 9$	0.4	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 9</u>	0.4	-	10	mA
ΙL	latching current	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G+}; $ T _j = 25 °C; <u>Fig. 10</u>	-	-	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; <u>Fig. 10</u>	-	-	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ T _j = 25 °C; <u>Fig. 10</u>	-	-	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ T _j = 25 °C; <u>Fig. 10</u>	-	-	15	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	10	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 13	-	-	1	V
		V _D = 800 V; I _T = 0.1 A; T _j = 125 °C; Fig. 13	0.2	-	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	-	0.5	mA
Dynamic ch	naracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit; Fig. 14	120	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T _j = 110 °C; dI _{com} / dt = 0.44 A/ms; gate open circuit	2	-	-	V/µs

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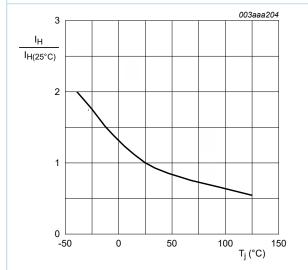
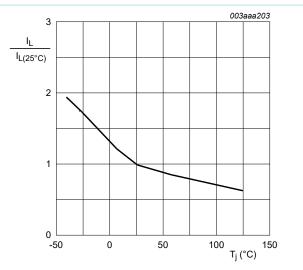
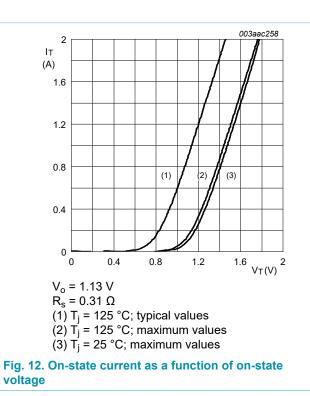


Fig. 11. Normalized holding current as a function of junction temperature

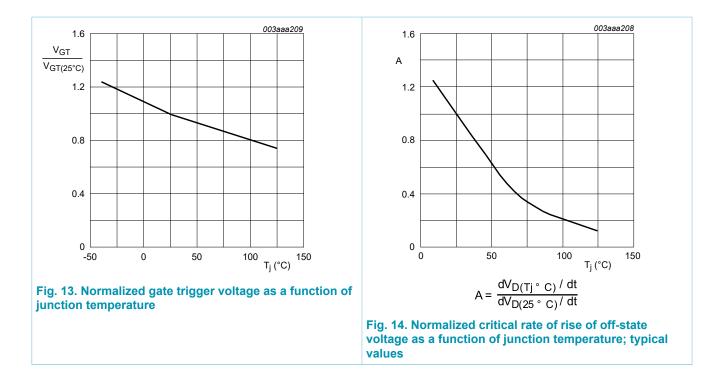




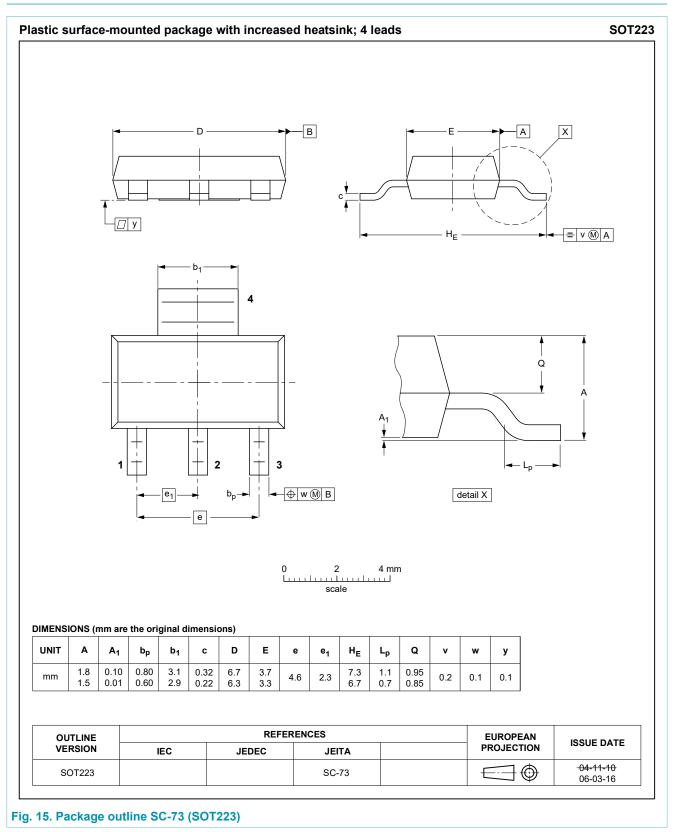


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10. Package outline



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11. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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